A Product Line of
Diodes Incorporated

PI6C5922504

2.5 GHz 1:4 LVDS Fanout Buffer with Internal Termination

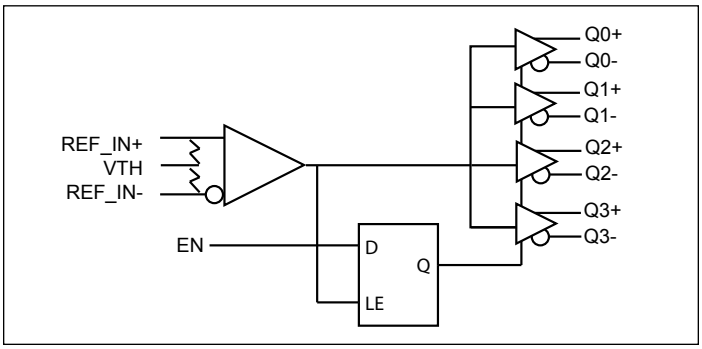
Features

- F_{MAX} < 2.5GHz
- 4 pairs of differential LVDS outputs
- Low additive jitter, < 0.05ps (max)
- Input CLK accepts: LVDS, LVDS, CML, SSTL input level
- Output to Output skew: <20ps
- Operating Temperature: -40°C to 85°C
- Power supply: 3.3V ±10% or 2.5V ±5%
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
  https://www.diodes.com/quality/product-definitions/
- Packaging (Pb-free & Green)
  - 16-pin, TQFN (ZH)

Description

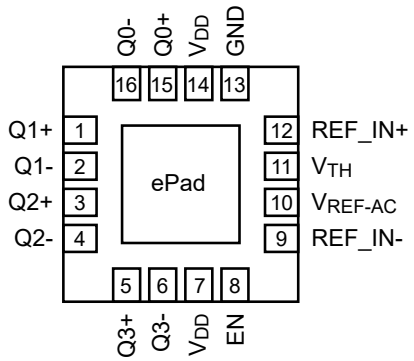
The PI6C5922504 is a high-performance low-skew 1-to-4 LVDS fanout buffer. The CLK inputs accept LVPECL, LVDS, CML and SSTL signals. PI6C5922504 is ideal for clock distribution applications such as providing fanout for low noise Diodes oscillators.

Block Diagram



Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Configuration



Pin Description

Pin #	Name	Type	Description
1, 2	Q1+, Q1-	Output	Differential output pair, LVDS interface level.
3, 4	Q2+, Q2-	Output	Differential output pair, LVDS interface level.
5, 6	Q3+, Q3-	Output	Differential output pair, LVDS interface level.
7, 14	V_{DD}	Power	Core Power Supply
8	EN	Input	Synchronous Output Enable, with internal 25kΩ pull-up resistor. Logic high selects enable, and logic low selects disable.
9	REF_IN-	Input	Differential IN negative input, AC and DC coupled
10	V_{REF-AC}	Output	Reference Voltage: Biased to V_{DD}-1.4V. Used when AC coupling inputs
11	V_{TH}	Output	Differential pair IN center-tap node. Tie to VREF-AC for AC Coupled inputs.
12	REF_IN+	Input	Differential IN positive input, AC and DC coupled
13	GND	Power	Ground
15, 16	Q0+, Q0-	Output	Differential output pair, LVDS interface level.
–	ePad	Power	Connect to GND

Functional Description

REF_IN+	REF_IN-	EN	Q+	Q-
0	1	1	0	1
1	0	1	1	0
X	X	0	0	1

Maximum Ratings

(Over operating free-air temperature range)

Storage Temperature	-65°C to+155°C
Junction Temperature	Max. 125°C
3.3V Core Supply Voltage	-0.5 to +4.6V
ESD Protection (HBM)	2000V

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{DD}	Power Supply Voltage		3.0		3.6	V
			2.375		2.625	V
T_A	Ambient Temperature		-40		85	°C
I_{DD}	Power Supply Current	@3.3V± 10%, loaded		88	105	mA
		@2.5V± 5% loaded		58	75	
R_{DIFF_IN}	Differential Input Resistance (IN+ to IN-)		90	100	110	Ω
V_{IH}	Input High Voltage		1.2		V_{DD} - 0.9	V
V_{IL}	Input Low Voltage		0.4		V_{IH}-0.1	V
V_{IN}	Input Voltage Swing		0.1		V_{DD}	V
V_{DIFF_IN}	Differential Input Swing		0.2			V
V_{REF-AC}	Output Reference Voltage		V_{DD} -1.5	V_{DD} -1.3	V_{DD} -1.15	V

LVCMOS/LVTTL DC Characteristics (T_A = -40°C to +85°C, V_{DD} = 2.5V ±5% to 3.3V ±10%)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	Input High Voltage		2.0		V_{DD}	V
V_{IL}	Input Low Voltage		0		0.8	
I_{IH}	Input High Current		-125		20	µA
I_{IL}	Input Low Current		-300			µA

LVDS DC Characteristics (T_A = -40°C to +85°C, V_{DD} = 3.3V ±10%, 2.5V ±5%)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{OUT}	Output Voltage Swing		250	325	400	mV
V_{DIFF_OUT}	Differential Output Voltage Swing		500	650	800	mV
V_{OCM}	Output Common Mode Voltage		1.15		1.35	V
Delta V_{OCM}	Change in Common mode Voltage		-100		100	mV

AC Characteristics (T_A = -40°C to +85°C, V_{DD} = 3.3V ±10%, 2.5V ±5%)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
f_{max}	Output Frequency			2.5		GHz
t_{pd}	Propagation Delay	V_{IN} < 400mV	370	470	570	ps
		V_{IN} ≥ 400mV	300	410	500	
T_{sk}	Output-to-output Skew(2)				20	ps
	Device to Device skew				200	ps
T_s	Setup time			150		ps
T_h	Hold time			150		ps
t_r/t_f	Output Rise/Fall time	20% - 80%	55		200	ps
t_{odc}	Output duty cycle	f ≤ 1 GHz	48		52	%
		1 GHz ≤ f < 2.5 GHz	40		60	%
V_{PP}	Output Swing	LVDS outputs	250		800	mV
t_j	Buffer additive jitter RMS	156.25MHz with 12KHz to 20MHz integration range(3)		30		fs

Notes:

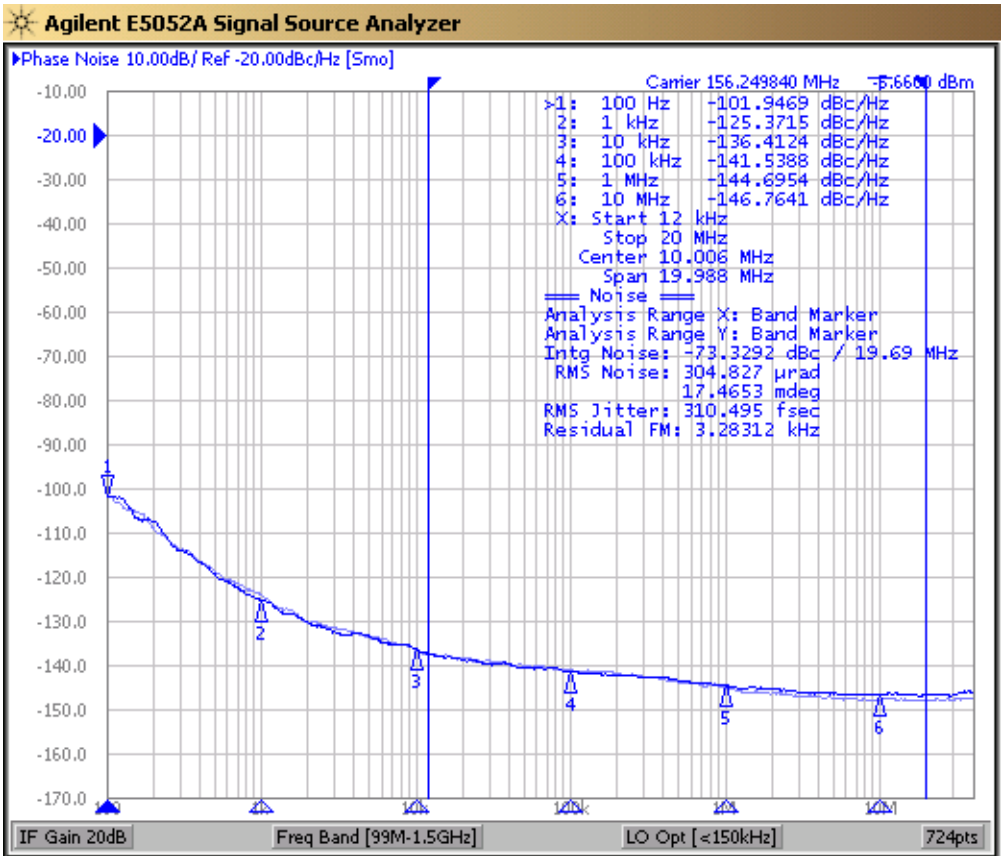
1. Measured from the differential input to the differential output crossing point
2. Defined as skew between outputs at the same supply voltage and with equal loads. Measured at the output differential crossing point
3. Input source phase noise similar to phase noise plot in page 5

Thermal Information

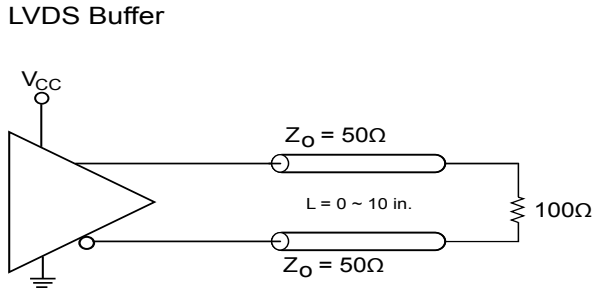
Symbol	Description	Condition	
Θ_{JA}	Junction-to-ambient thermal resistance	Still air	57.7 °C/W
Θ_{JC}	Junction-to-case thermal resistance		32.2 °C/W

Note: Thermal data accounts for ePad being connected to GND.

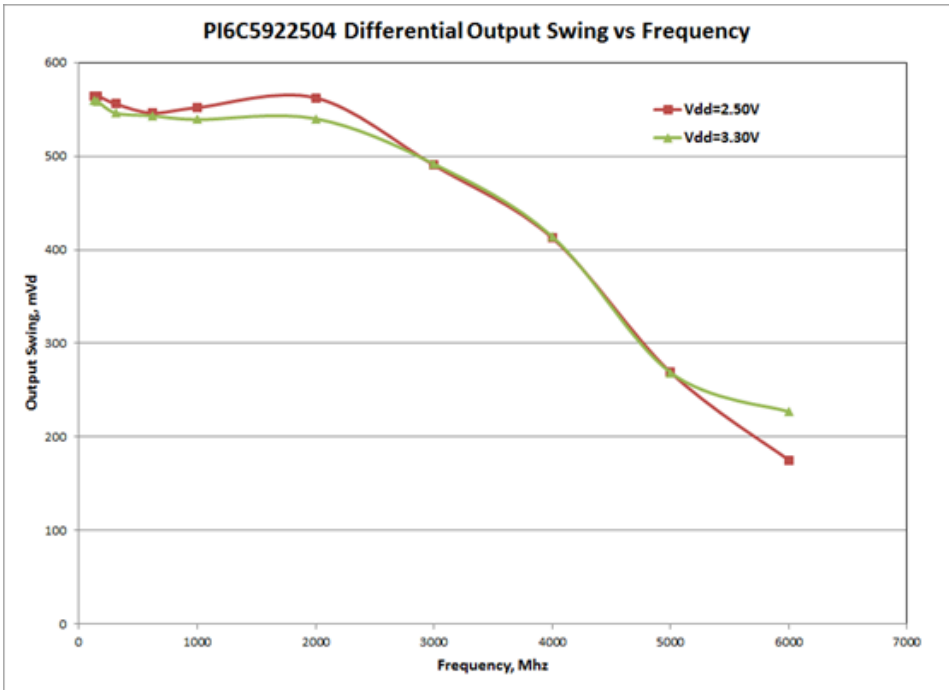
Phase Noise Plots



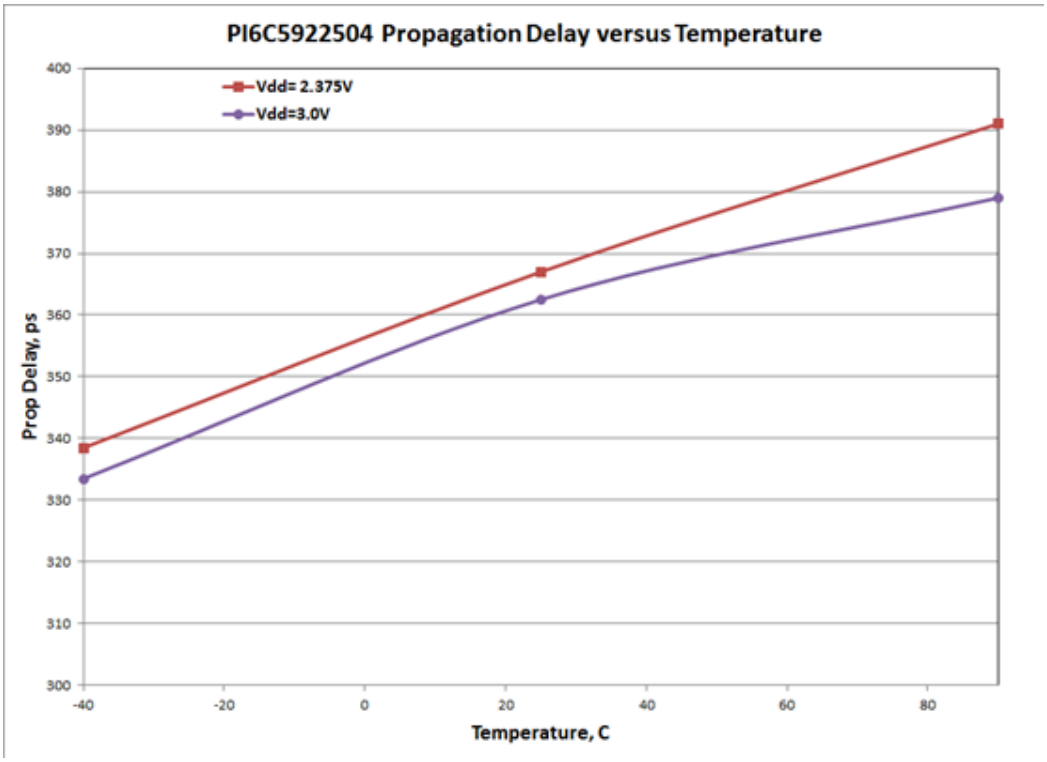
Configuration Test Load Board Termination for LVDS Outputs



Output Swing vs Frequency



Propagation Delay vs Temperature



Application Information

Suggest for Unused Inputs and Outputs

LVCMOS Input Control Pins

It is suggested to add pull-up=4.7k and pull-down=1k for LVCMOS pins even though they have internal pull-up/down but with much higher value (>=50k) for higher design reliability.

REF_IN=/ REF_IN- Input Pins

They can be left floating if unused. For added reliability, connect 1kΩ to GND.

Outputs

All unused outputs are suggested to be left open and not connected to any trace. This can lower the IC power supply power.

Power Decoupling & Routing

VDD Pin Decoupling

As general design rule, each VDD pin must have a 0.1uF decoupling capacitor. For better decoupling, 1uF can be used. Locating the decoupling capacitor on the component side has better decoupling filter result as shown in Fig. 1.

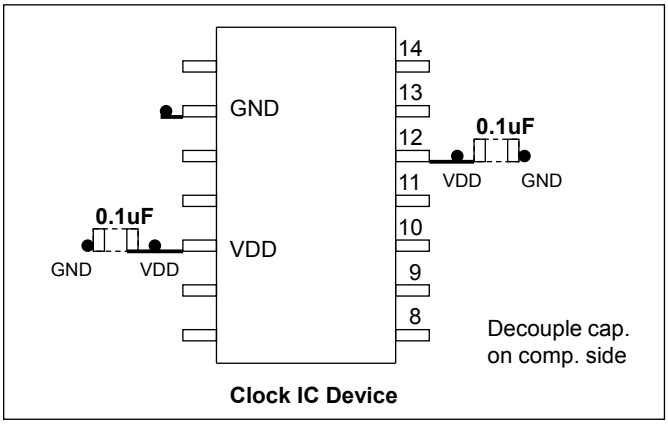


Figure 1: Placement of Decoupling Caps

Differential Clock Trace Routing

Always route differential signals symmetrically, make sure there is enough keep-out space to the adjacent trace (>20mil.). In 156.25MHz XO drives IC example, it is better routing differential trace on component side as the following Fig. 2.

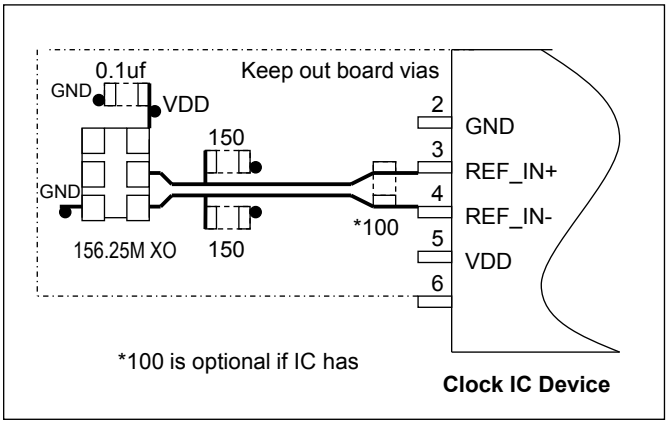


Figure 2: IC Routing for XO Drive

Clock timing is the most important component in PCB design, so its trace routing must be planned and routed as a first priority in manual routing. Some good practices are to use minimum vias (total trace vias count <4), use independent layers with good reference plane and keep other signal traces away from clock traces (>20mil.) etc.

LVPECL and LVDS Input Interface

LVPECL and LVDS DC Input

LVPECL and LVDS clock input to this IC is connected as shown in the Fig. 3.

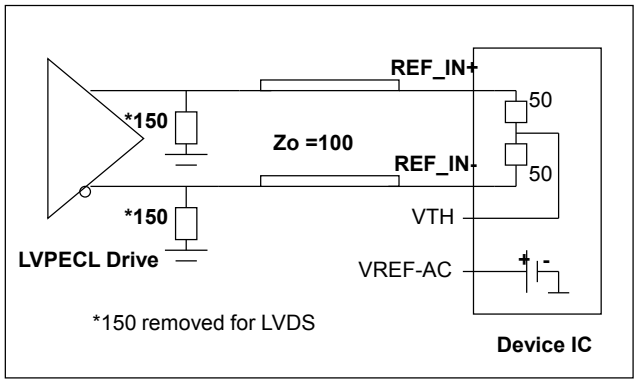


Figure 3: LVPECL/ LVDS Input

LVPECL and LVDS AC Input

LVPECL and LVDS AC drive to this clock IC requires the use of the VREF-AC output to recover the DC bias for the IC input as shown in Fig. 4

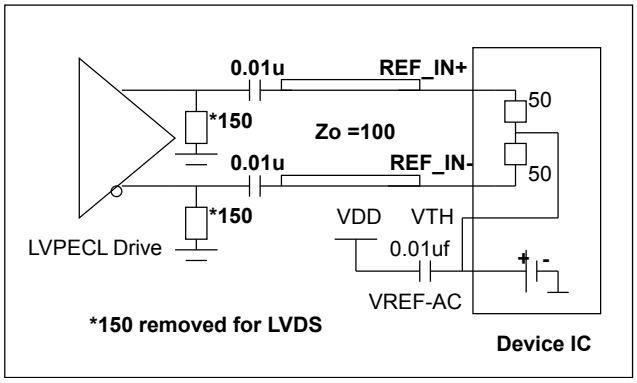


Figure 4: LVPECL/ LVDS AC Coupled Input

CML AC-Coupled Input

CML AC-coupled drive requires a connection to VREF-AC as shown in Fig. 5. The CML DC drive is not recommended as different vendors have different CML DC voltage level. CML is mostly used in AC coupled drive configuration for data and clock signals.

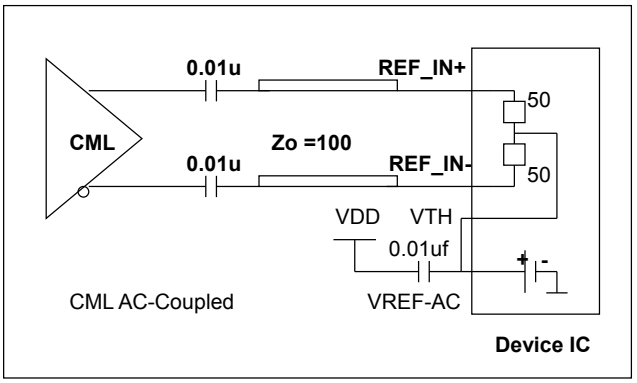


Figure 5: CML AC-Coupled Input Interface

HCSL AC-Coupled Input

It is suggested to use AC coupling to buffer PCIe HCSL 100MHz clock since its V_cm is relatively low at about 0.4V, as shown in Fig. 6.

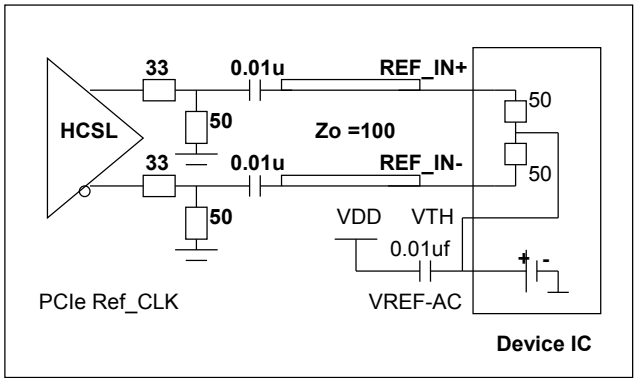
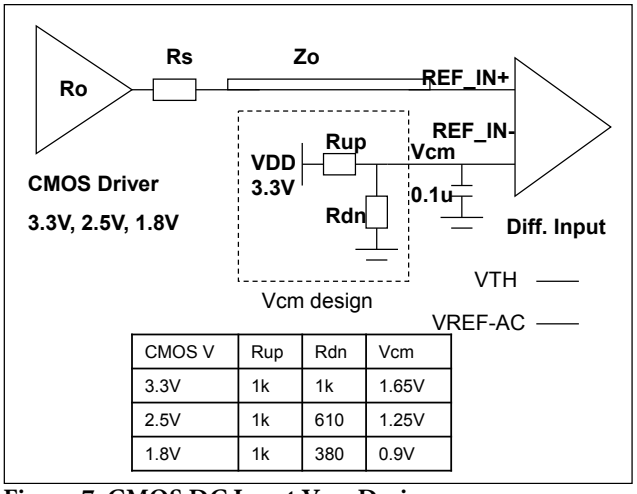


Figure 6: HCSL AC-Coupled Input Interface

CMOS Clock DC Drive Input

LVCMOS clock has voltage Voh levels such as 3.3V, 2.5V, 1.8V. CMOS drive requires a Vcm design at the input: Vcm= ½ (CMOS V) as shown in Fig. 7. Rs =22 ~33Ω typically.



CMOS V	Rup	Rdn	Vcm
3.3V	1k	1k	1.65V
2.5V	1k	610	1.25V
1.8V	1k	380	0.9V

Figure 7: CMOS DC Input Vcm Design

Device LVPECL Output Terminations

LVPECL Output Popular Termination

The most popular LVPECL termination is 150Ω pull-down bias and 100Ω across at RX side. Please consult ASIC datasheet if it already has 100Ω or equivalent internal termination. If so, do not connect external 100Ω across as shown in Fig. 8. This popular termination's advantage is that it does not allow any bias through from V_{DD}. This prevents V_{DD} system noise coupling onto clock trace.

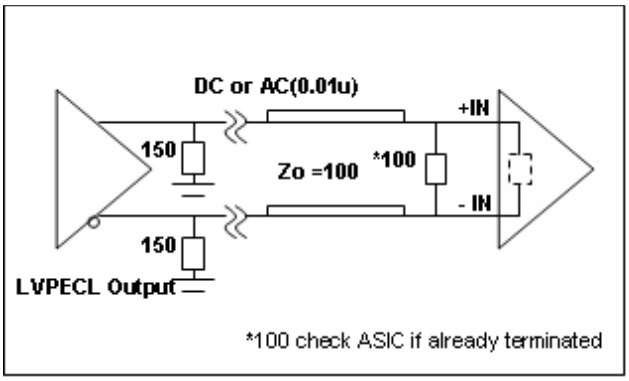


Figure. 8 LVPECL Output Popular Termination

LVPECL Output Thevenin Termination

Fig. 9 shows LVPECL output Thevenin termination which is used for shorter trace drive (<5in.), but it takes V_{DD} bias current and V_{DD} noise can get onto clock trace. It also requires more component count. So it is seldom used today.

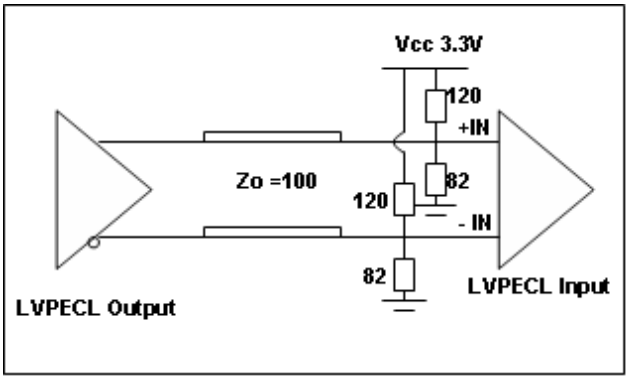


Figure. 9 LVPECL Thevenin Output Termination

LVPECL Output AC Thevenin Termination

LVPECL AC Thevenin terminations require a 150Ω pull-down before the AC coupling capacitor at the source as shown in Fig. 10. Note that pull-up/down resistor value is swapped compared to Fig. 9. This circuit is good for short trace (<5in.) application only.

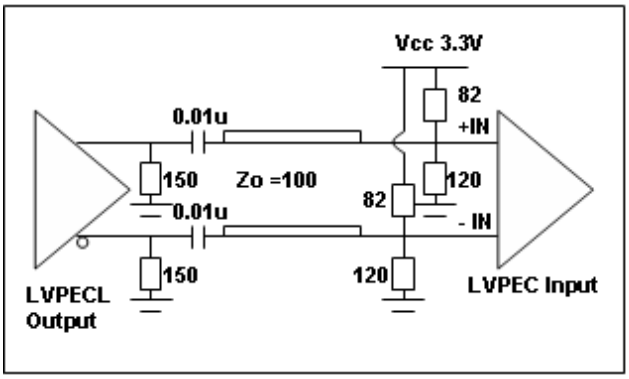


Figure. 10 LVPECL Output AC Thenvenin Termination

LVPECL Output Drive HCSL Input

Using the LVPECL output to drive a HCSL input can be done using a typical LVPECL AC Thenvenin termination scheme. Use pull-up/down 450/60Ω to generate Vcm=0.4V for the HCSL input clock. This termination is equivalent to 50Ω load as shown in Fig. 11.

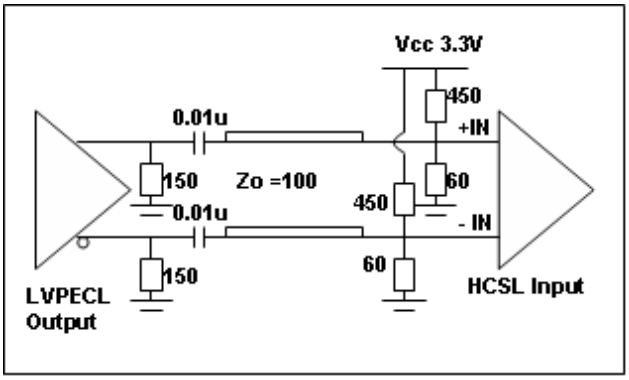


Figure. 11 LVPECL Output Drive HCSL Termination

LVPECL Output V_swing Adjustment

It is suggested to add another cross 100Ω at TX side to tune the LVPECL output V_swing without changing the optimal 150Ω pull-down bias in Fig. 12. This form of double termination can reduce the V_swing in ½ of the original at the RX side. By fine tuning the 100Ω resistor at the TX side with larger values like 150 to 200Ω, one can increase the V_swing by > 1/2 ratio.

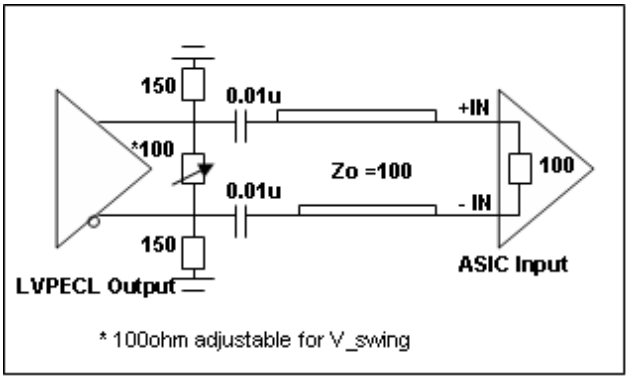


Figure. 12 LVPECL Output V_swing Adjustment

Clock Jitter Definitions

Total jitter= RJ + DJ

Random Jitter (RJ) is unpredictable and unbounded timing noise that can fit in a Gaussian math distribution in RMS. RJ test values are directly related with how long or how many test samples are available. Deterministic Jitter (DJ) is timing jitter that is predictable and periodic in fixed interference frequency. Total Jitter (TJ) is the combination of random jitter and deterministic jitter: , where is a factor based on total test sample count. JEDEC std. specifies digital clock TJ in 10k random samples.

Phase Jitter

Phase noise is short-term random noise attached on the clock carrier and it is a function of the clock offset from the carrier, for example dBc/Hz@10kHz which is phase noise power in 1-Hz normalized bandwidth vs. the carrier power @10kHz offset. Integration of phase noise in plot over a given frequency band yields RMS phase jitter, for example, to specify phase jitter <=1ps at 12k to 20MHz offset band as SONET standard specification.

Device Thermal Calculation

Fig. 13 shows the JEDEC thermal model in a 4-layer PCB.

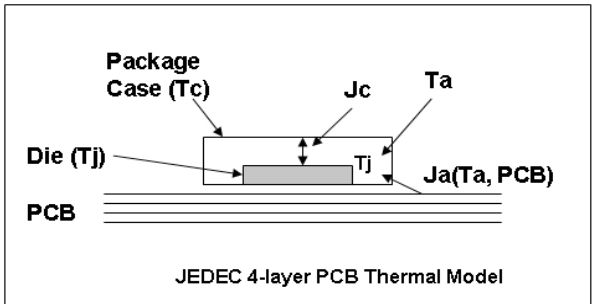


Figure. 13 JEDEC IC Thermal Model

Important factors to influence device operating temperature are:

1) The power dissipation from the chip (P_chip) is after subtracting power dissipation from external loads. Generally it can be the no-load device Idd

2) Package type and PCB stack-up structure, for example, 1oz 4 layer board. PCB with more layers and are thicker has better heat dissipation

3) Chassis air flow and cooling mechanism. More air flow M/s and adding heat sink on device can reduce device final die junction temperature Tj

The individual device thermal calculation formula:

Tj =Ta + Pchip x Ja

Tc = Tj - Pchip x Jc

Ja ___ Package thermal resistance from die to the ambient air in C/W unit; This data is provided in JEDEC model simulation. An air flow of 1m/s will reduce Ja (still air) by 20~30%

Jc ___ Package thermal resistance from die to the package case in C/W unit

Tj ___ Die junction temperature in C (industry limit <125C max.)

Ta ___ Ambiant air température in C

Tc ___ Package case temperature in C

Pchip___ IC actually consumes power through Iee/GND current

Thermal calculation example

To calculate Tj and Tc of PI6CV304 in an SOIC-8 package:

Step 1: Go to Diodes web to find Ja=157 C/W, Jc=42 C/W

https://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Step 2: Go to device datasheet to find Idd=40mA max.

I_{DD}	Supply Current	C_L = 33pF/33MHz		20		mA
		C_L = 33pF/66MHz		40		
		C_L = 22pF/80MHz		35		
		C_L = 15pF/100MHz		32		
		C_L = 10pF/125MHz		28		
		C_L = 10pF/155MHz		41		

Step 3: P_total= 3.3Vx40mA=0.132W

Step 4: If Ta=85C

Tj= 85 + Ja xP_total= 85+25.9 = 105.7C

Tc= Tj + Jc xP_total= 105.7- 5.54 = 100.1C

Note:

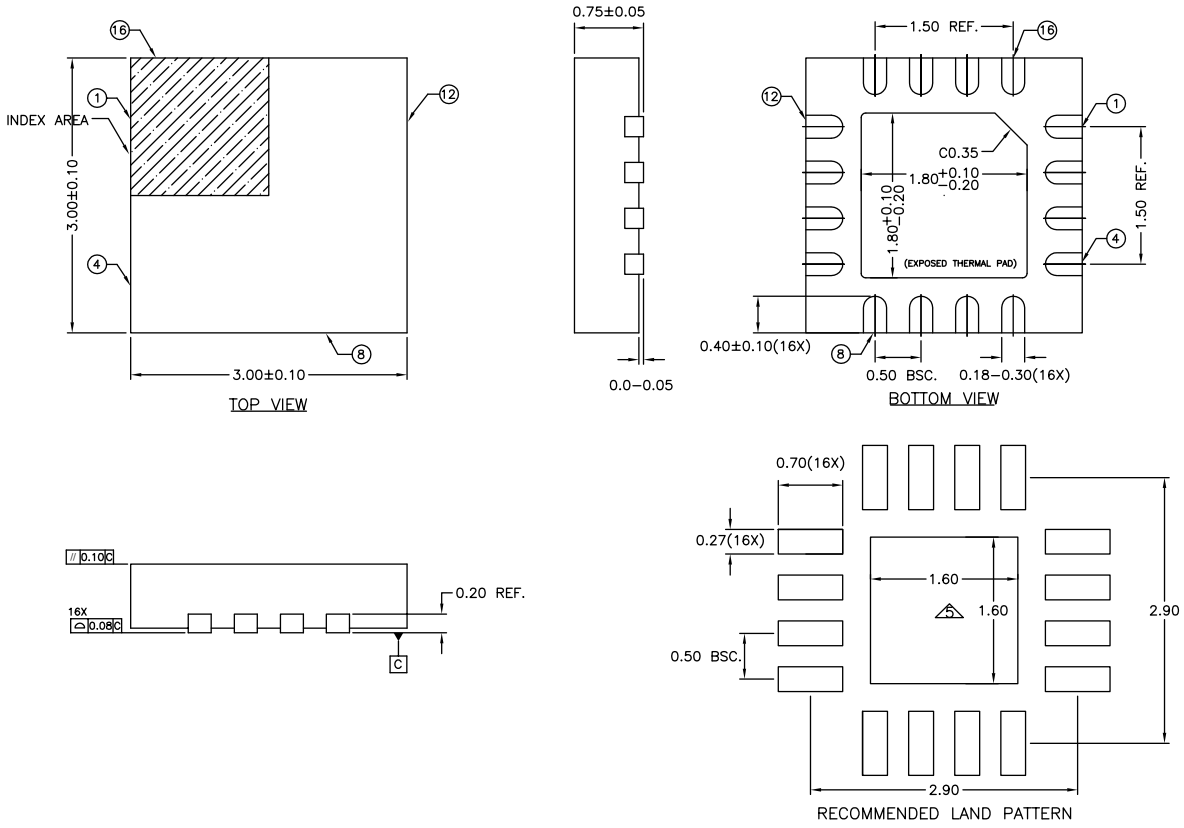
The above calculation is directly using Idd current without subtracting the load power, so it is a conservative estimation. For more precise thermal calculation, use P_unload or P_chip from device Iee or GND current to calculate Tj, especially for LVPECL buffer ICs that have a 150Ω pull-down and equivalent 100Ω differential RX load.

Part Marking

YY: Year
WW: Workweek
1st X: Assembly Code
2nd X: Fab Code

Packaging Mechanical

16-TQFN (ZH)



NOTE :
1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
2. COPLANARITY APPLIES TO THE EXPOSED THERMAL PAD AS WELL AS THE TERMINALS.
3. REFER JEDEC MO–220
4. RECOMMENDED LAND PATTERN IS FOR REFERENCE ONLY.
5. THERMAL PAD SOLDERING AREA (MESH STENCIL IS RECOMMENDED).

20-1297

DIODES INCORPORATED / PERICOM ENABLING SERIAL CONNECTIVITY	DATE: 06/17/20
DESCRIPTION: 16-contact, TQFN (W-QFN3030-16)	
PACKAGE CODE: ZH (ZH16)	
DOCUMENT CONTROL #: PD-2047	REVISION: F

For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Ordering Information

Ordering Code	Package Code	Package Description
PI6C5922504ZHIEX	ZH	16-Contact, Thin Fine Pitch Quad Flat No-Lead (TQFN)

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. I = Industrial
5. E = Pb-free and Green
6. X suffix = Tape/Reel

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